

Silicon PNP Power Transistors

D45H10

DESCRIPTION

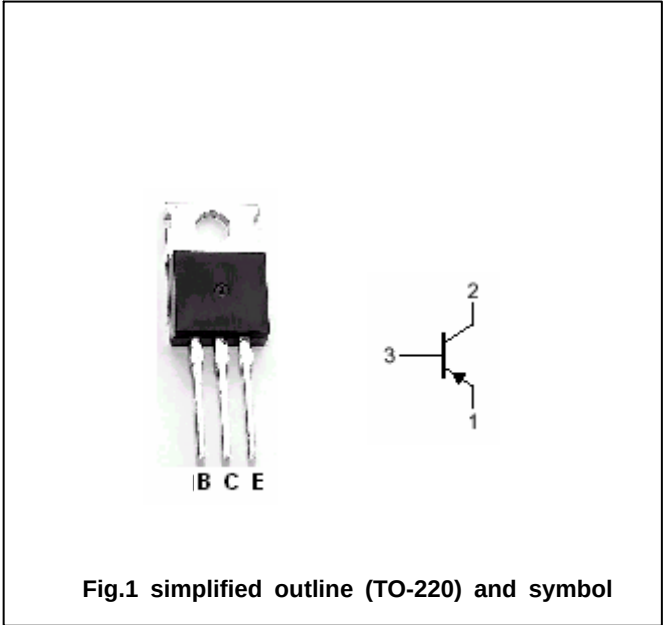
- With TO-220C package
- Fast switching speeds
- Low collector saturation voltage

APPLICATIONS

- For general purpose power amplifications and switching regulators,converters and power amplifiers applications

PINNING

PIN	DESCRIPTION
1	Emitter
2	Collector;connected to mounting base
3	Base



Absolute maximum ratings (Tc=25°C)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	-80	V
V_{CEO}	Collector-emitter voltage	Open base	-80	V
V_{EBO}	Emitter-base voltage	Open collector	-5	V
I_C	Collector current (DC)		-10	A
I_{CM}	Collector current-Peak		-20	A
P_D	Total power dissipation	$T_C=25^{\circ}C$	50	W
		$T_a=25^{\circ}C$	1.67	
T_j	Junction temperature		150	$^{\circ}C$
T_{stg}	Storage temperature		-55~150	$^{\circ}C$

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	VALUE	UNIT
$R_{th\ j-C}$	Thermal resistance from junction to case	2.5	$^{\circ}C/W$

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CHARACTERISTICS

Tj=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CEO(SUS)}$	Collector-emitter sustaining voltage	$I_C=-10mA$ $I_B=0$,	-80			V
V_{CEsat}	Collector-emitter saturation voltage	$I_C=-8A$; $I_B=-0.8A$			-1.0	V
V_{BEsat}	Base-emitter saturation voltage	$I_C=-8A$; $I_B=-0.8A$			-1.5	V
I_{CES}	Collector cut-off current	$V_{CE}=-80V$; $V_{BE}=0$			-10	μA
I_{EBO}	Emitter cut-off current	$V_{EB}=-5V$; $I_C=0$			-0.1	mA
h_{FE-1}	DC current gain	$I_C=-2A$; $V_{CE}=-1V$	35			
h_{FE-2}	DC current gain	$I_C=-4A$; $V_{CE}=-1V$	20			
f_T	Transition frequency	$I_C=-0.5A$; $V_{CE}=-10V$		40		MHz
C_{cb}	Collector capacitance	$f=1MHz$; $V_{CB}=-10V$		230		pF

Switching times

t_{on}	Turn-on time	$I_C=-5A$ $I_{B1}=-I_{B2}=-0.5A$		135		ns
t_s	Storage time			0.5		μs
t_f	Fall time			0.1		μs

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PACKAGE OUTLINE

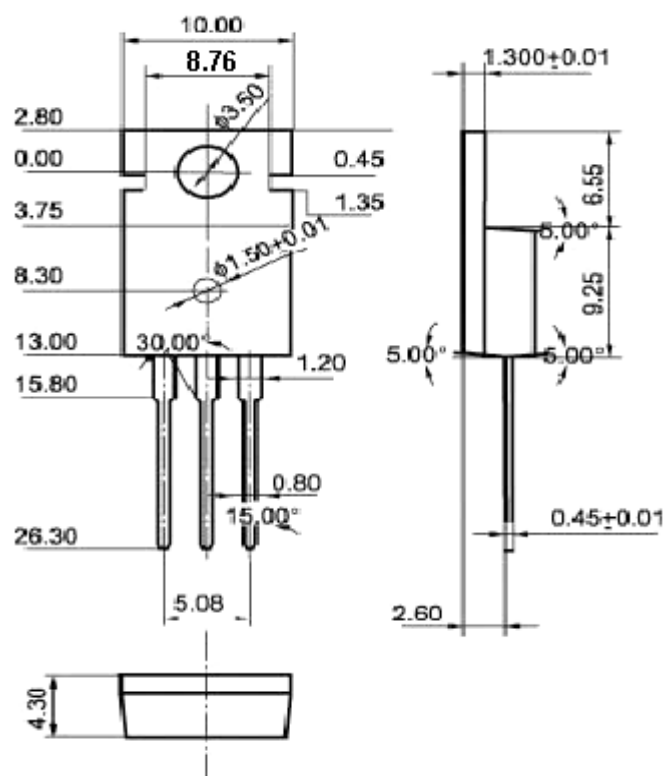


Fig.2 Outline dimensions (unindicated tolerance: $\pm 0.10\text{mm}$)